

INFORMATION DISCLOSURE STATEMENT PTO-1449	Atty. Docket No. 031111	Serial No. New Application
	Applicant(s): Mitsuaki HORI, et al.	
	Filing Date: September 16, 2003	Group Art Unit: Not Yet Assigned

U.S. PATENT DOCUMENTS

Examiner Initial		Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
<u>AS</u>	AA	6,215,146	Umeda et al.	04/10/01			
_____	AB						
_____	AC						
_____	AD						

FOREIGN PATENT DOCUMENTS


		Document No.	Date	Country	Translation (Yes or No)
<u>AS</u>	AE	11-204787	07/30/99	Japan	Yes-Abstract/Discussed in the specification
_____	AF				
_____	AG				
_____	AH				
_____	AI				

OTHER DOCUMENTS

_____	AJ	
_____	AK	
Examiner	<u>AS</u>	Date Considered 12/05/04

INFORMATION DISCLOSURE CITATION PTO-1449	Atty. Docket No. 031111	Serial No. 10/662,384
	Applicant(s): HORI, et al.	
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U.S. PATENT DOCUMENTS

Examiner Initial	Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
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<u>LS-</u> 	A K AL	Chen et al., Downscaling Limit of Equivalent Oxide Thickness in Formation of Ultrathin Gate Dielectric by Thermal-Enhanced Remote Plasma Nitridation, IEEE TRANSACTIONS ON ELECTRON DEVICES, May 2002, Vol. 49, No.5, P,840-845
Examiner	<u>AG</u>	Date Considered <u>10/5/04</u>